

Bipolar Transistor and Method of Producing same**ABSTRACT**

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In a method of producing a bipolar transistor, a semiconductor substrate having a substrate surface is provided. A base-terminal layer for providing a base terminal is formed on the substrate surface, and an emitter window having a wall area is formed in the base-terminal layer. A first spacing layer is formed on the wall area of the emitter contact window, and a recess is etched into the substrate within a window specified by the first spacing layer. A base layer contacted by outdiffusion from the base-terminal layer is formed in the recess of the emitter window, and a second spacing layer is formed on the first spacing layer and on the base layer. The second spacing layer is structured for the purpose of specifying a planar terminal pad on the base layer, and an emitter layer is formed on the planar terminal pad.

Fig. 2